TOSHIBA Transistor Silicon NPN Triple Diffused Mesa Type

# 2SC5716

Horizontal Deflection Output for High Resolution Display, Color TV

• High voltage: V<sub>CBO</sub> = 1700 V

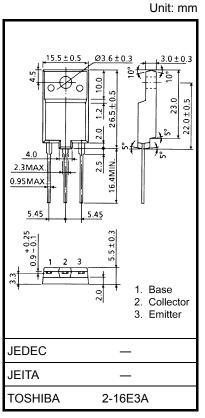
• High speed:  $t_f(2) = 0.2 \mu s$  (typ.)

• Collector metal (fin) is fully covered with mold resin.

#### **Absolute Maximum Ratings (Tc = 25°C)**

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		$V_{CBO}$	1700	V	
Collector-emitter voltage		V <sub>CEO</sub>	700	V	
Emitter-base voltage		V <sub>EBO</sub>	5	٧	
Collector current	DC	IC	8	Α	
	Pulse	I <sub>CP</sub>	16		
Base current		ΙΒ	4	Α	
Collector power dissipation		PC	55	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55~150	°C	

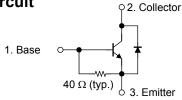
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



Weight: 5.5 g (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

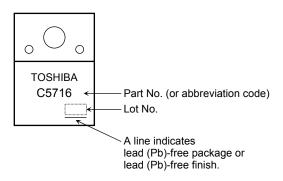
### **Equivalent Circuit**

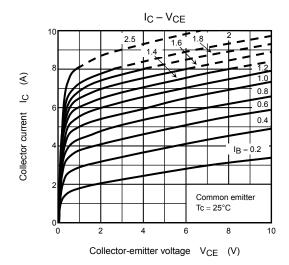


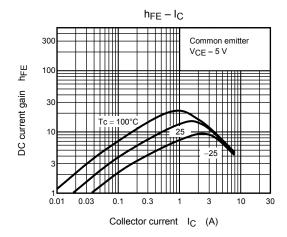
## **Electrical Characteristics (Tc = 25°C)**

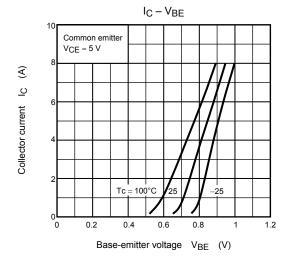
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cut-off current		I <sub>CBO</sub>	V <sub>CB</sub> = 1700 V, I <sub>E</sub> = 0	_	_	1	mA	
Emitter cut-off current		I <sub>EBO</sub>	V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0	83	_	250	mA	
Emitter-base breakdown voltage		V (BR) EBO	I <sub>E</sub> = 400 mA, I <sub>B</sub> = 0	5	_	_	V	
DC current gain		h <sub>FE</sub> (1)	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 1 A	6	_	20		
		h <sub>FE</sub> (2)	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 6 A	3.8	_	9		
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	I <sub>C</sub> = 6 A, I <sub>B</sub> = 1.5 A	_	_	5	V	
Base-emitter saturation voltage		V <sub>BE</sub> (sat)	I <sub>C</sub> = 6 A, I <sub>B</sub> = 1.5 A	_	0.9	1.2	V	
Forward voltage (damper diode)		V <sub>F</sub>	I <sub>F</sub> = 6 A	_	1.3	1.8	V	
Transition frequency		f <sub>T</sub>	V <sub>CE</sub> = 10 V, I <sub>C</sub> = 0.1 A	_	2	_	MHz	
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	180	_	pF	
Switching time	Storage time	t <sub>stg</sub> (1)	I <sub>CP</sub> = 6 A, I <sub>B1 (end)</sub> = 1.2 A,	_	6	8	- μ <b>s</b>	
	Fall time	t <sub>f</sub> (1)	ICP = 6 A, I <sub>B1 (end)</sub> = 1.2 A, f <sub>H</sub> = 15.75 kHz	_	0.3	0.6		
	Storage time	t <sub>stg</sub> (2)	I <sub>CP</sub> = 5.5 A, I <sub>B1 (end)</sub> = 1.1 A,		3.5	5		
	Fall time	t <sub>f</sub> (2)	f <sub>H</sub> = 31.5 kHz		0.2	0.35		

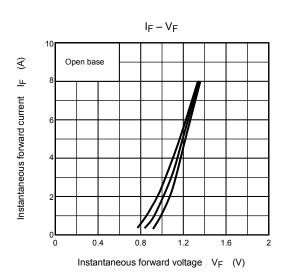
## Marking



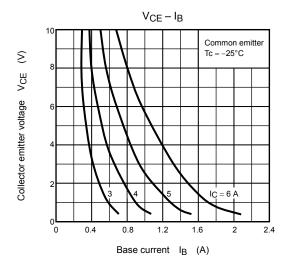


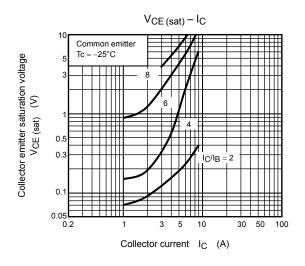


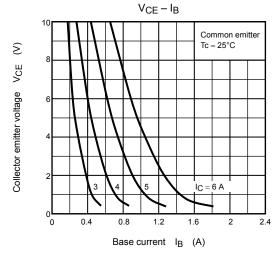


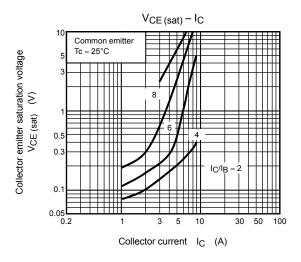


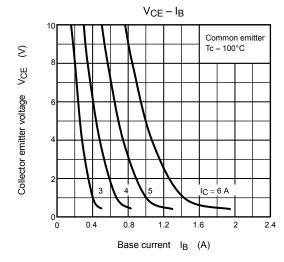
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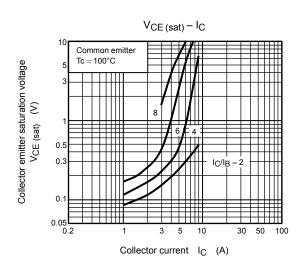


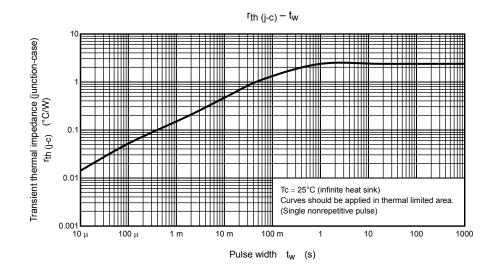


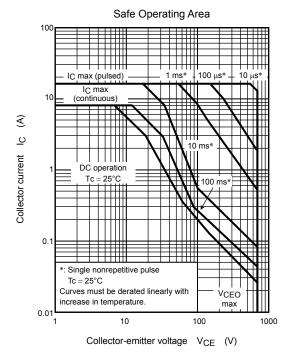


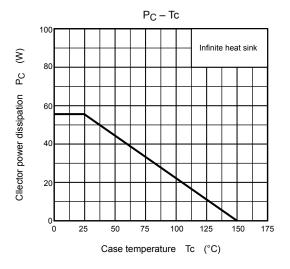












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